

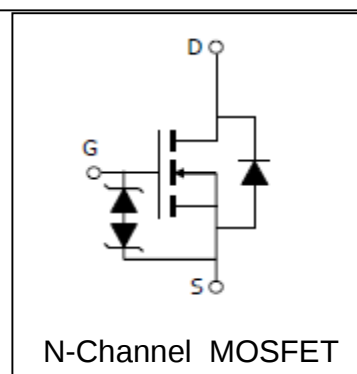
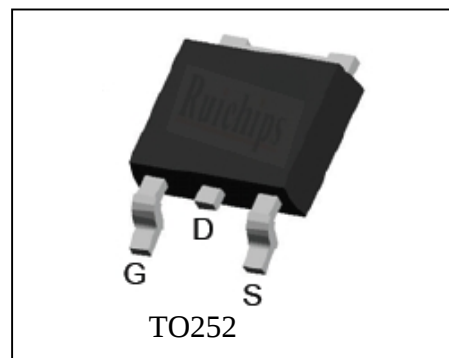
Features

- 100V/16A,
 $R_{DS(ON)} = 70m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 85m\Omega(Typ.)@V_{GS}=4.5V$
- Super High Dense Cell Design
- ESD protected
- Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)

Applications

- Power Management.

Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	16	A
Mounted on Large Heat Sink				
I _{DP}	300μs Pulse Drain Current Tested	T _C =25°C	64 ^①	A
I _D	Continuous Drain Current(V _{GS} =10V)	T _C =25°C	16 ^②	A
		T _C =100°C	11	
P _D	Maximum Power Dissipation	T _C =25°C	50	W
		T _C =100°C	25	
R _{θJC}	Thermal Resistance-Junction to Case		3	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^③	Avalanche Energy, Single Pulsed		70	mJ

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU1HE16L			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} =0V			1	μA
		T _J =85°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.5	2	2.7	V
I _{GSS}	Gate Leakage Current	V _{GS} =±16V, V _{DS} =0V			±10	μA
R _{DS(ON)} ^④	Drain-Source On-state Resistance	V _{GS} = 10V, I _{DS} =5A		70	90	mΩ
		V _{GS} = 4.5V, I _{DS} =2A		85	120	mΩ
Diode Characteristics						
V _{SD} ^④	Diode Forward Voltage	I _{SD} =5A, V _{GS} =0V			1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =5A, dI _{SD} /dt=100A/μs		40		ns
Q _{rr}	Reverse Recovery Charge			70		nC
Dynamic Characteristics ^⑤						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		1.8		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} = 50V, Frequency=1.0MHz		840		pF
C _{oss}	Output Capacitance			70		
C _{rss}	Reverse Transfer Capacitance			40		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =50V, R _L =30Ω, I _{DS} =5A, V _{GEN} = 10V, R _G =6Ω		10		ns
t _r	Turn-on Rise Time			13		
t _{d(OFF)}	Turn-off Delay Time			28		
t _f	Turn-off Fall Time			15		
Gate Charge Characteristics ^⑤						
Q _g	Total Gate Charge	V _{DS} =80V, V _{GS} = 10V, I _{DS} =5A		18		nC
Q _{gs}	Gate-Source Charge			4		
Q _{gd}	Gate-Drain Charge			5		

Notes: ① Pulse width limited by safe operating area.

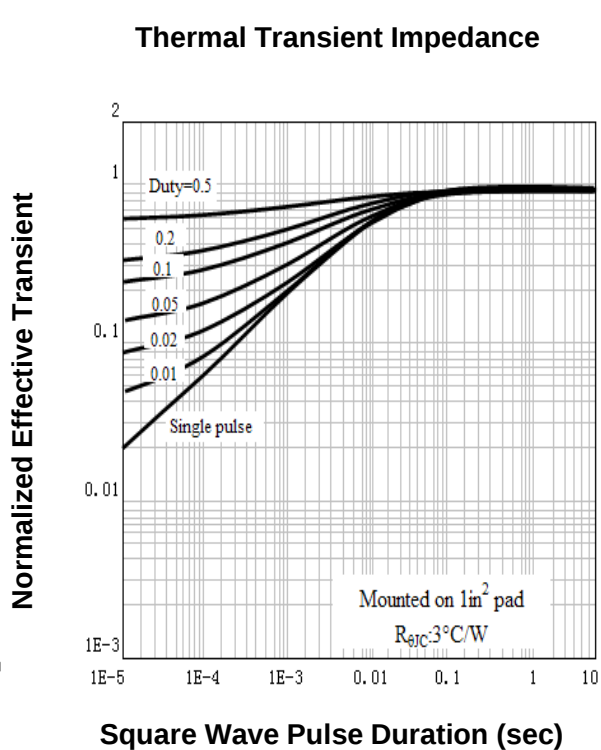
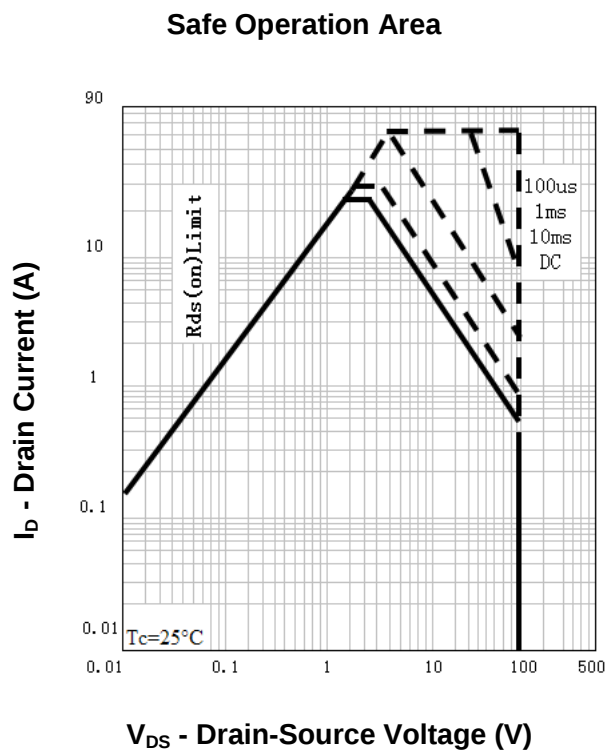
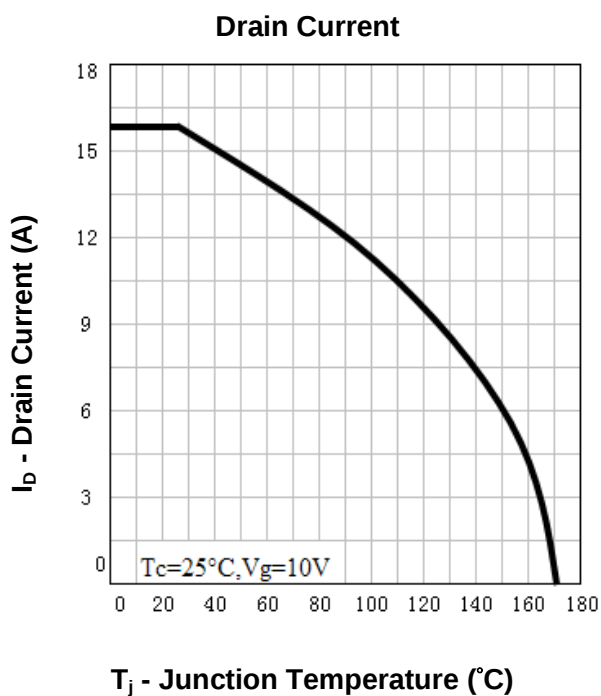
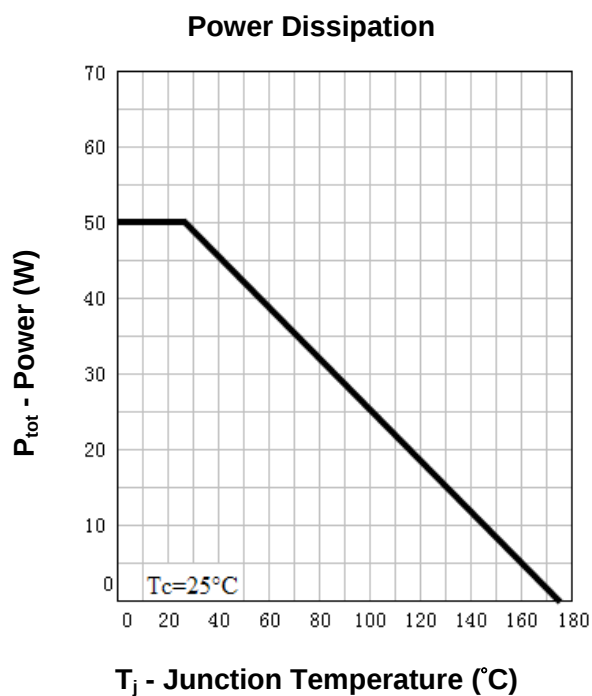
② Calculated continuous current based on maximum allowable junction temperature. Current limited by bond wire.

③ Limited by T_{Jmax} , $I_{AS}=17A$, $V_{DD}=48V$, $R_G=50\Omega$, Starting $T_J=25^{\circ}\text{C}$.

④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

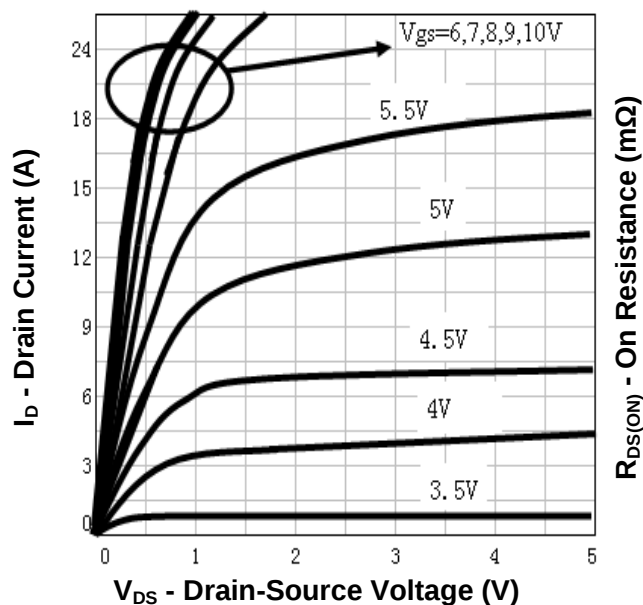
⑤ Guaranteed by design, not subject to production testing.

Typical Characteristics

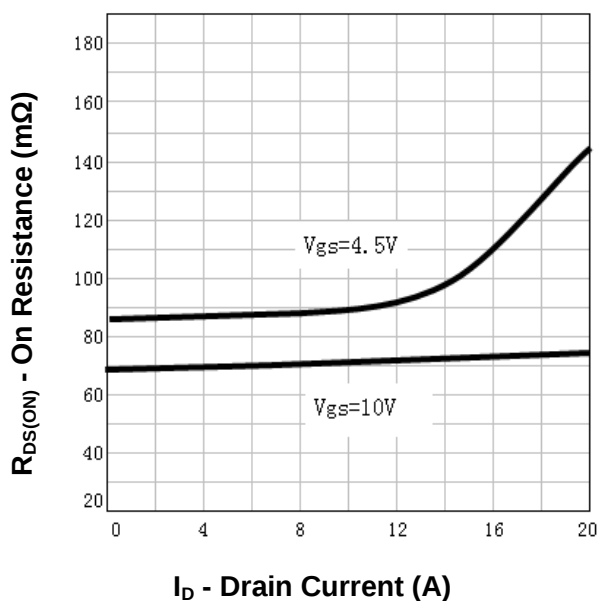


Typical Characteristics

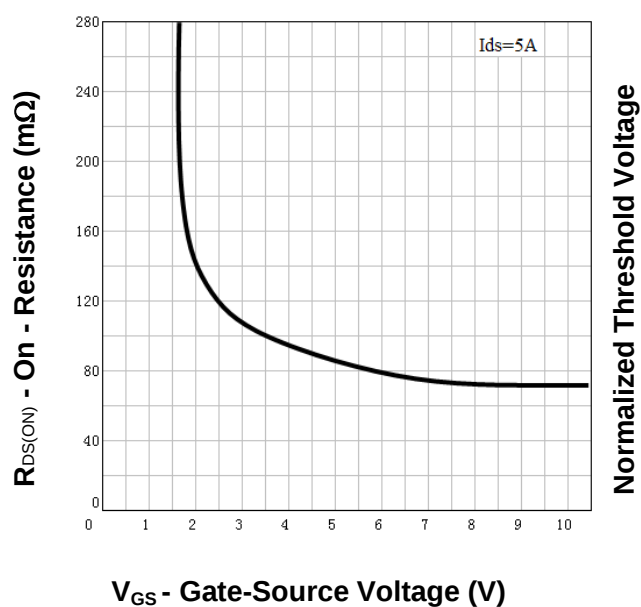
Output Characteristics



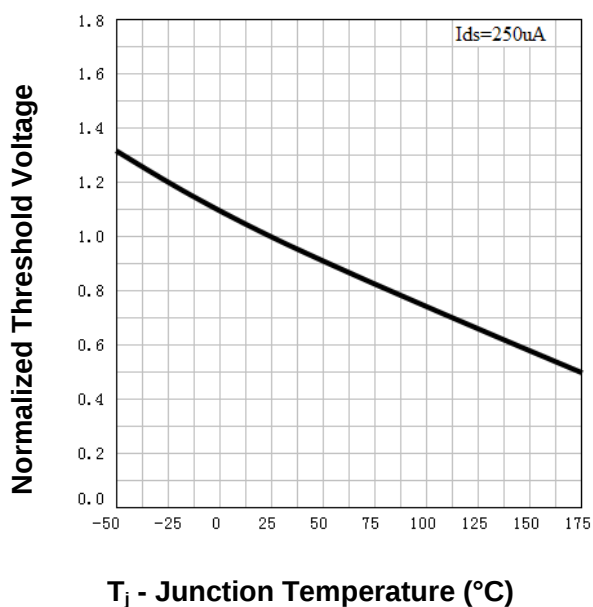
Drain-Source On Resistance



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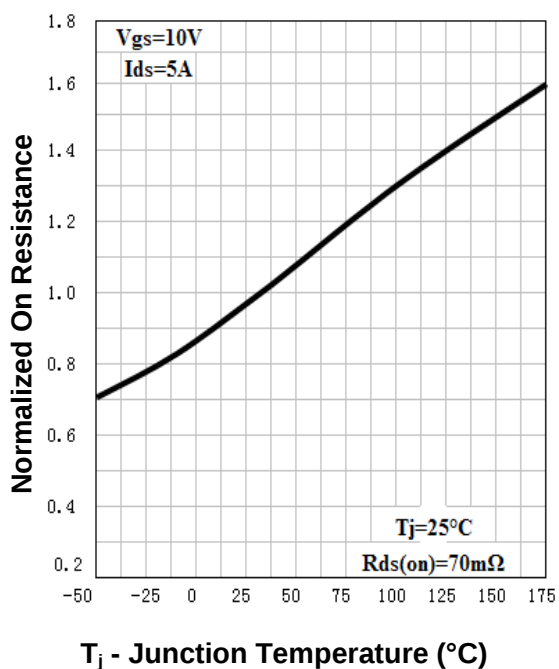


Gate Threshold Voltage

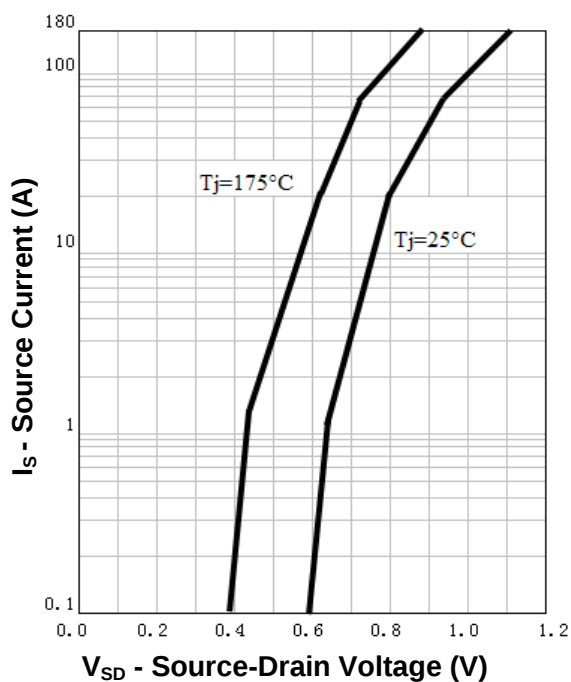


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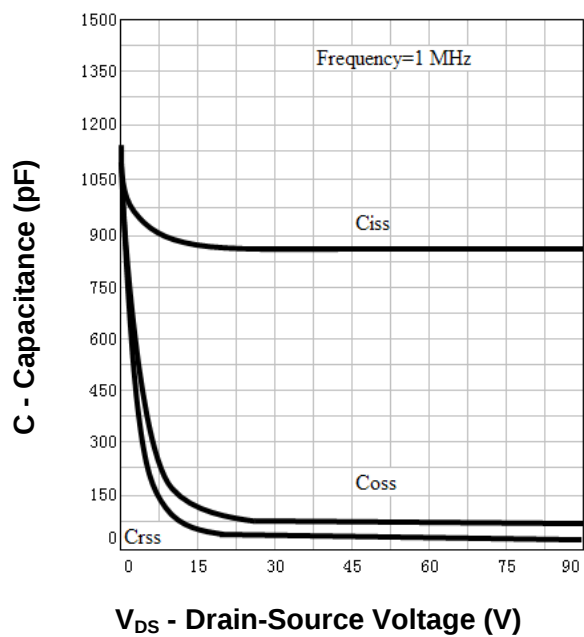
Drain-Source On Resistance



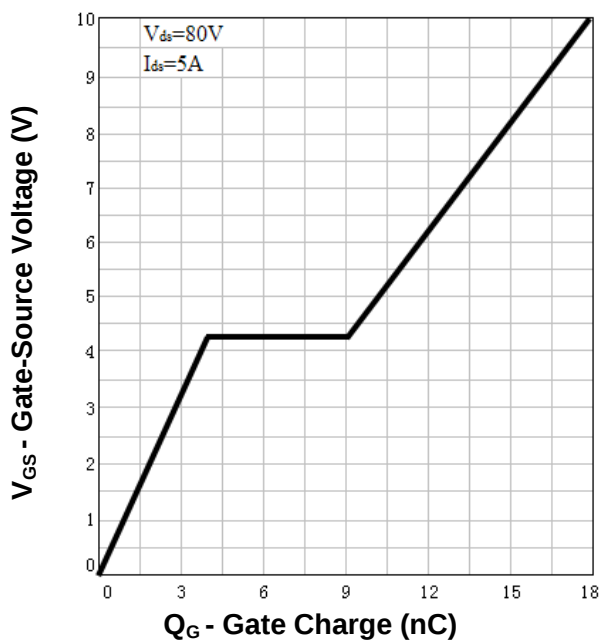
Source-Drain Diode Forward



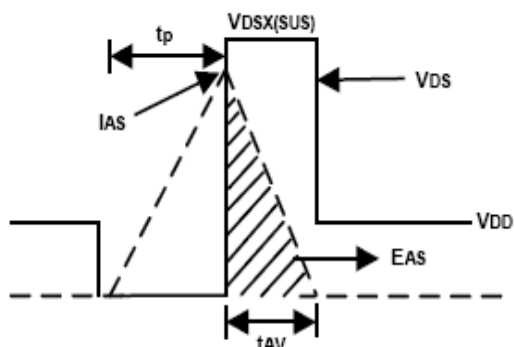
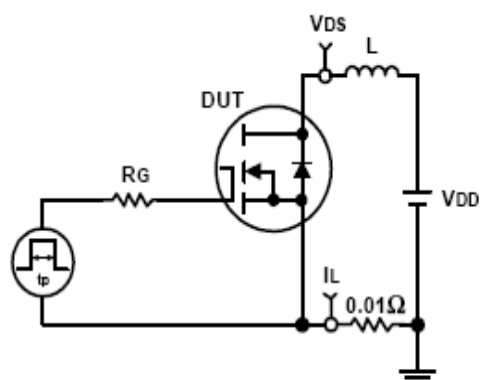
Capacitance



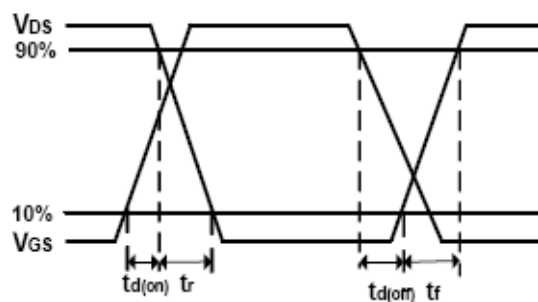
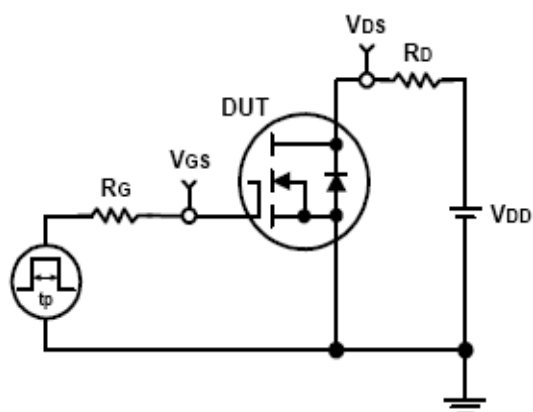
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

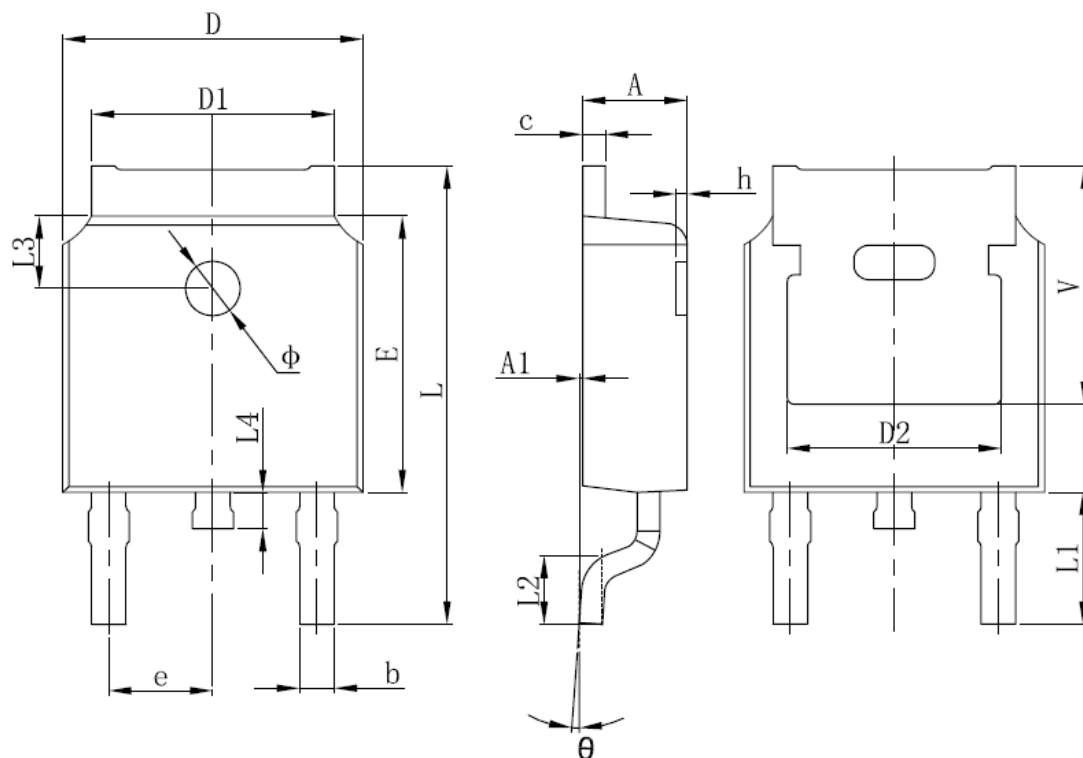


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU1HE16L	RU1HE16L	TO-252	Tape&Reel	2500	13''	16mm

Package Information

TO252-2L



SYMBOL	MM		INCH		SYMBOL	MM		INCH	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	2.200	2.400	0.087	0.094	L	9.800	10.400	0.386	0.409
A1	0.000	0.127	0.000	0.005	L1	2.900 REF.		0.114 REF.	
b	0.660	0.860	0.026	0.034	L2	1.400	1.700	0.055	0.067
C	0.460	0.580	0.018	0.023	L3	1.600 REF.		0.063 REF.	
D	6.500	6.700	0.256	0.264	L4	0.600	1.000	0.024	0.039
D1	5.100	5.460	0.201	0.215	Φ	1.100	1.300	0.043	0.051
D2	4.830 REF.		0.190 REF.		θ	0°	8°	0°	8°
E	6.000	6.200	0.236	0.244	h	0.000	0.300	0.000	0.012
e	2.186	2.386	0.086	0.094	V	5.350 REF.		0.211 REF.	

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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